IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

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Serial No.: unknown

Filed: unknown

For: A METHOD FOR MAKING A SEMICONDUCTOR DEVICE WITH A METAL GATE ELECTRODE

Art Unit: unknown

Examiner: unknown

Attorney Docket: P18611

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

This Information Disclosure Statement is being submitted under 37 C.F.R. §1.97(b). Enclosed is a copy of Information Disclosure Citation Form PTO-1449 together with copies of the references cited on that form. It is respectfully requested that the cited references be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

Pursuant to 37 C.F.R. § 1.97, the submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made and is not to be construed as an admission that the information cited in this statement constitutes prior art or is otherwise material to patentability.

Respectfully submitted,

Dated: March 22, 2004

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Form PTO-1449 (Modified)	Atty Docket No.: P18611	Serial No.: Unknown
List of Patents and Publications Statement (Use several sheets if necessary)		Applicant: Uday Shah et al.
		Filing Date: March 22, 2004

REFERENCE DESIGNATION		U.S. PATENT DOCUMENTS				
Examiner Initials		Document No.		Class	Sub-Class	Filing date if appropriate
	AA	6,063,698	Tseng et al.	438	585	
	AB	6,184,072 B1	Kaushik et al.	438	197	
	AC	6,420,279 B1	Ono et al.	438	785	
	AD	6,475,874 B2	Xiang et al.	438	396	
	AE	6,514,828 B2	Ahn et al.	438	240	
	AF	6,544,906 B2	Rotondaro et al.	438	785	
	AG	6,617,209 B1	Chau et al.	438	240	
	AH	6,617,210 B1	Chau et al.	438	240	
	AI	6,620,713 B2	Arghavani et al.	438	585	
	AJ	6,689,675 B1	Parker et al.	438	585	
	AK	6,696,327 B1	Brask et al.	438	197	
	AL	6,696,345 B2	Chau et al.	438	387	
	AM	US2002/0197790 A1	Kizilyalli et al.	438	240	
	AN	US2003/0032303 A1	Yu et al.	438	770	
	AO	US2003/0045080 A1	Visokay et al.	438	591	
	AP					

FOREIGN PATENT DOCUMENTS

		Document No.	Date	Country	Class	Sub-Class	Translation
	AQ						
	AR						

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

	AS	Polishchuk et al., "Dual Workfunction CMOS Gate Technology Based on Metal Interdiffusion", www.eesc.berkeley.edu, 1 page
	AT	Doug Barlage et al., "High-Frequency Response of 100nm Integrated CMOS Transistors with High-K Gate Dielectrics", 2001 IEEE, 4 pages
	AU	Lu et al., "Dual-Metal Gate Technology for Deep-Submicron CMOS Devices", dated April 29, 2003, 1 page
	AV	Schwantes et al., "Performance Improvement of Metal Gate CMOS Technologies with Gigabit Feature Sizes", Technical University of Hanburg-Harburg, 5 pages
	AW	Brask et al., "A Method for Making a Semiconductor Device Having a Metal Gate Electrode," Serial No. 10/704,497, Filed November 6, 2003
	AX	Brask et al., "A Method for Etching a Thin Metal Layer", Serial No. 10/704,498, Filed November 6, 2003
	AY	Brask et al., "A Method for Making a Semiconductor Device with a Metal Gate Electrode that is Formed on an Annealed High-K Gate Dielectric Layer", Serial No. 10/742,678, Filed December 19, 2003
	AZ	

Examiner	Date Considered

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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